

Radiation	Type	Technology	Electrodes
Deep red	solderable	AlGaAs/GaAs	N (cathode) up

	typ. dimensions (μm)
	<p>typ. thickness 260 (±20) μm</p> <p>cathode gold alloy, 1.5 μm</p> <p>anode gold alloy, 0.5 μm</p>

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		1.7	2.0	V
Forward voltage	I _F = 300 mA	V _F		2.0	2.4	V
Reverse voltage	I _R = 10 μA	V _R	5			V
Radiant power	I _F = 20 mA	Φ _e	1.0	1.4		mW
Radiant power ¹	I _F = 300 mA	Φ _e	12	17		mW
Radiant power ²	I _F = 300 mA	Φ _e		33		mW
Peak wavelength	I _F = 300 mA	λ _p	685	700	710	nm
Spectral bandwidth at 50%	I _F = 300 mA	Δλ _{0.5}		40		nm
Switching time	I _F = 100 mA	t _r , t _f		40/30		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Quantity
ELC-685-21-05				

Packing: Chips on adhesive film with wire-bond side on top